

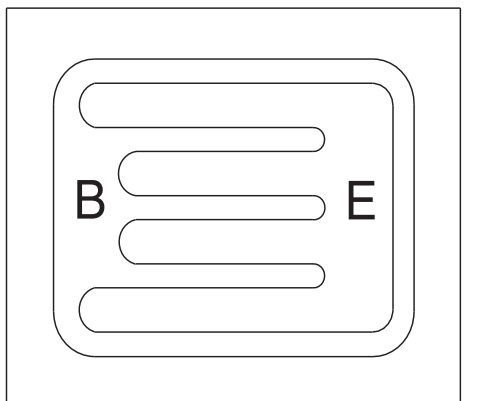
PROCESS CP211
Power Transistor
 NPN - Amp/Switch Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 x 99 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 48 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Cr/Ni/Ag 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

1,450

PRINCIPAL DEVICE TYPES

2N3054A

CJD41C

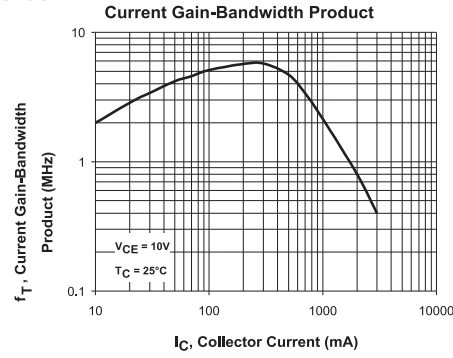
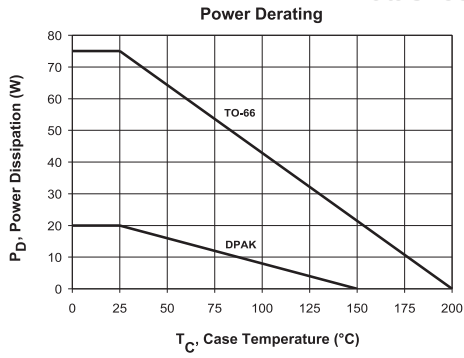
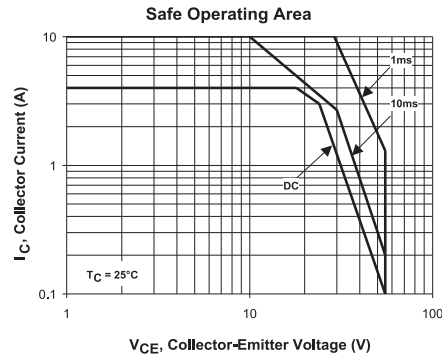
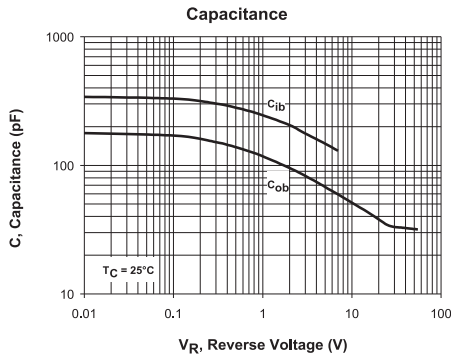
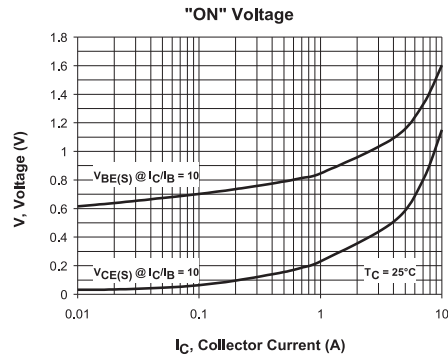
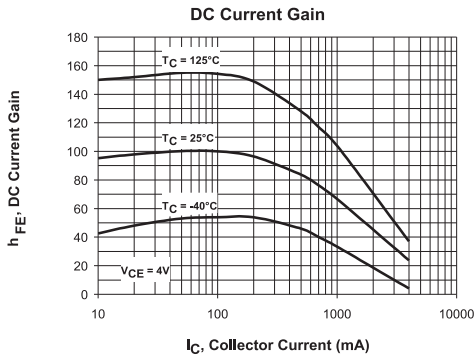
TIP41C

eet4U.com

DataSheet

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